

## **isc** Silicon NPN Power Transistor

# 2SD1882

#### DESCRIPTION

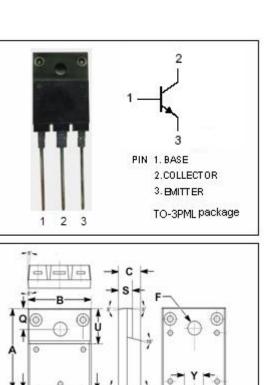
- High Breakdown Voltage-
  - : V<sub>CBO</sub>= 1500V (Min)
- High Switching Speed
- High Reliability
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## APPLICATIONS

- Color TV horizontal deflection output
- Color display horizontal deflection output

ABSOLUTE N	MUMIXAN	RATINGS(Ta=	<b>25°</b> C)
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PARAMETER	VALUE	UNIT
Collector-Base Voltage	1500	v
Collector-Emitter Voltage	800	V
Emitter-Base Voltage	6	V
Collector Current- Continuous	3	A
Collector Current-Pulse	12	A
Collector Power Dissipation @ $T_c=25^{\circ}C$	50	W
Junction Temperature	150	°C
Storage Temperature Range	-55~150	°C
	Collector-Base Voltage   Collector-Emitter Voltage   Emitter-Base Voltage   Collector Current- Continuous   Collector Current-Pulse   Collector Power Dissipation   @ Tc=25°C   Junction Temperature	Collector-Base Voltage1500Collector-Emitter Voltage800Emitter-Base Voltage6Collector Current- Continuous3Collector Current-Pulse12Collector Power Dissipation @ Tc=25°C50Junction Temperature150



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	m	m	1
DIM	MIN	MAX	
Α	19.90	20.10	1
В	15.75	16.10	1
С	5.50	5.70	1
D	0.90	1.10	1
F	3.30	3.50	]
G	2.90	3.20	]
н	5.90	6.10	]
J	0.595	0.70	]
Κ	21.10	22.50	
L	1.90	2.25	]
N	10.80	11.00	
Q	4.90	5.10	
Ŗ	3.75	3.95	
S	3.20	3.60	
U Y	9.90	10.10	
	4.20 1.90	4.90	
Z	1.90	2.10	



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### ELECTRICAL CHARACTERISTICS

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA; I <sub>B</sub> = 0	800			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 0.6A			5.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 0.6A			1.5	V
I <sub>СВО</sub>	Collector Cutoff Current	V <sub>CB</sub> = 800V; I <sub>E</sub> = 0			10	μA
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CE</sub> = 1500V; R <sub>BE</sub> = 0			1.0	mA
Іево	Emitter Cutoff Current	V <sub>EB</sub> = 4V; I <sub>C</sub> = 0			1.0	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 5V	8			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 2A; V <sub>CE</sub> = 5V	3			
t <sub>f</sub>	Fall Time	I <sub>C</sub> = 3A, I <sub>B1</sub> = 0.8A; I <sub>B2</sub> = -1.6A			0.3	μ <b>S</b>

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